

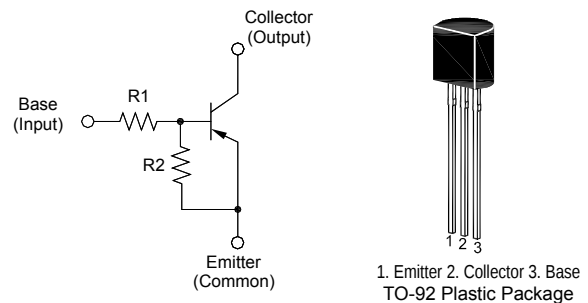
RA221S...RA226S

PNP Silicon Epitaxial Planar Transistors

for high current switching, interface circuit and driver circuit application.

Feature

- With Built-in Bias Resistor
- Simplify Circuit Design
- Reduce a Quantity of Parts and Manufacturing Process

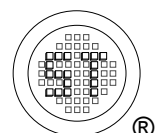


Resistor Values

Type	R1 (K Ω)	R2 (K Ω)
RA221S	1	1
RA222S	2.2	2.2
RA223S	4.7	4.7
RA224S	10	10
RA225S	1	10
RA226S	2.2	10

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Output Voltage		$-V_o$	50	V
Input Voltage	RA221S	$-V_i$	10, -10	V
	RA222S		12, -10	
	RA223S		20, -10	
	RA224S		30, -10	
	RA225S		10, -5	
	RA226S		12, -6	
Output Current		$-I_o$	300	mA
Total Power Dissipation		P_{tot}	200	mW
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	- 55 to + 150	$^\circ\text{C}$

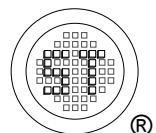


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Characteristics at $T_a = 25\text{ °C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_O = 5\text{ V}$, $-I_O = 50\text{ mA}$	G_I	33 39 47 56 56 56	- - - - - -	- - - - - -	- - - - - -
Output Cutoff Current at $-V_O = 30\text{ V}$	$-I_{O(OFF)}$	-	-	10	μA
Input Current at $-V_I = 5\text{ V}$	$-I_I$	- - - - - -	- - - - - -	7.2 3.8 1.8 0.88 7.2 3.6	mA
Output Voltage at $-I_O = 10\text{ mA}$, $-I_I = 0.5\text{ mA}$	$-V_{O(ON)}$	-	-	0.3	V
Input Voltage (ON) at $-V_O = 0.3\text{ V}$, $-I_O = 20\text{ mA}$	$-V_{I(ON)}$	- - - - - -	- - - - - -	3 3 3 3 3 2	V
Input Voltage (OFF) at $-V_O = 5\text{ V}$, $-I_O = 0.1\text{ mA}$	$-V_{I(OFF)}$	0.5 0.3	- -	- -	V
Transition Frequency at $-V_O = 10\text{ V}$, $-I_O = 5\text{ mA}$, $f = 100\text{ MHz}$	$f_T^{1)}$	-	200	-	MHz

¹⁾ Characteristic of transistor only.



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